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(71) Applicant *(for all designated States except US)*: **THIN FILM ELECTRONICS ASA** [NO/NO]; P.O. Box 1872 Vika, N-0124 Oslo (NO).

(71) Applicant and
(72) Inventor *(for all designated States except US)*: **WANG, Jianna** [CN/US]; 5 Dolores Ave., Waltham, MA 02452 (US).

(72) Inventor; and
(75) Inventor/Applicant *(for US only)*: **JACKSON, Thomas** [US/US]; 1348 Deerfield Drive, State College, PA 16801 (US).

(74) Agent: **LEISTAD, Geirr, I.**; Thin Film Electronics ASA, P.O. Box 1872 Vika, N-0124 Oslo (NO).

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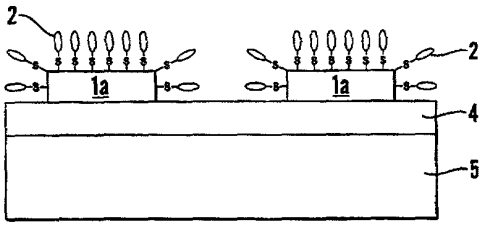
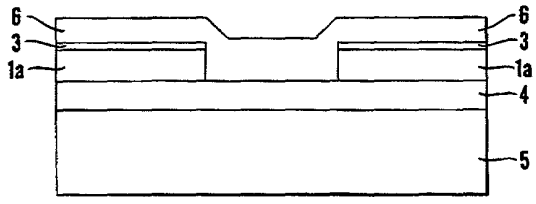
(54) Title: A MEANS FOR ELECTRICAL CONTACTING OR ISOLATION OF ORGANIC OR INORGANIC SEMICONDUCTORS AND A METHOD FOR ITS FABRICATION





(57) Abstract: In a means for electrical contacting or isolation of organic or inorganic semiconductors in electronic and optoelectronic devices, particularly thin-film devices, the means comprises a substrate (1) in the form of a contact material (1a) or an isolating material (4). A charge transfer material (2) is provided patterned or unpatterned on or at the surface of the substrate and includes charge transfer components in the form of donors and/or acceptors. The charge transfer material forms a self-assembling layer (3) on one or more atomic and/or molecular layers. The charge transfer material (2) has a direct or indirect bond to the surface of the substrate (1) and further forms a charge transfer complex with a thereabove adjacently provided organic or inorganic semiconductor (6). The charge transfer material (2) then forms a donor or acceptor material in the charge transfer complex depending upon respectively whether the semiconductor (6) itself is an acceptor or donor material.

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